Automotive TOGGLE switch

Description

The bipolar integrated circuit, U 6032 B, is designed as a TOGGLE switch. It controls an electrical load, for

Features

- Debounce time: 0.3 ms to 6 s
- RC oscillator determines switching characteristics
- Relay driver with Z-diode
- Debounced input for toggle switch

example, fog lamp, high/ low beam or heated windows for automotive applications. It has a defined power-on status.

- Two debounced inputs: ON and OFF
- Load dump protection
- RF interference protected
- Protection according to ISO/TR7637-1 (VDE 0839)



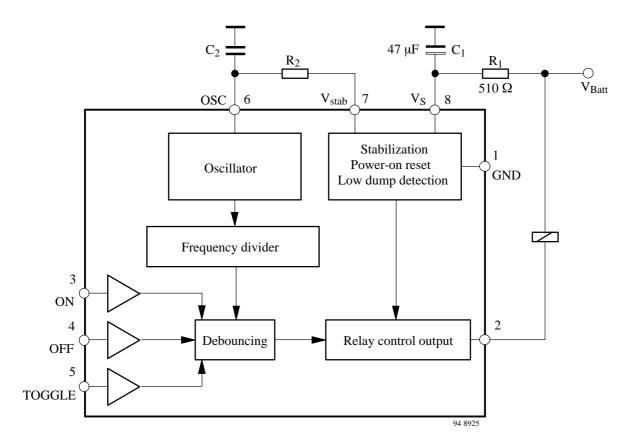


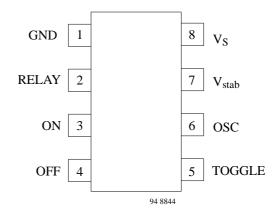
Figure 1 Block diagram with external circuit

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Pin	Symbol	Function
1	GND	Reference point, ground
2	RELAY	Relay control output
3	ON	Switch-on input
4	OFF	Switch-off input
5	TOGGLE	Toggle input
6	OSC	RC oscillator input
7	V _{stab}	Stabilized voltage
8	Vs	Supply voltage

Pin Configuration



Functional description

Power supply, Pin 8

For reasons of interference protection and surge immunity, the supply voltage (Pin 8) must be provided with an RC circuit as shown in figure 2a. Dropper resistor, R_1 , limits the current in case of overvoltage, whereas C_1 smoothes the supply voltage at Pin 8.

The integrated Z-diode (14 V) protects the supply voltage, V_S , therefore, the operation of the IC is possible between 6 V and 16 V, supplied by V_{Batt} .

However, it is possible to operate the integrated circuit with a 5 V supply, but it should be free of interference voltages. In this case, Pin 7 is connected to Pin 8 as shown in figure 2b, and the R_1C_1 circuit is omitted.

Recommended values are: $R_1 = 510 \Omega$, $C_1 = 47 \mu F$.

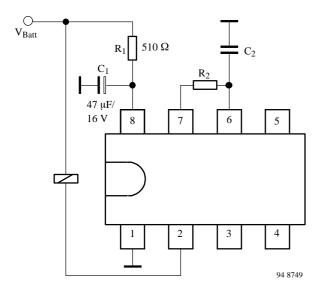


Figure 2a Basic circuit for 12 V supply and oscillator

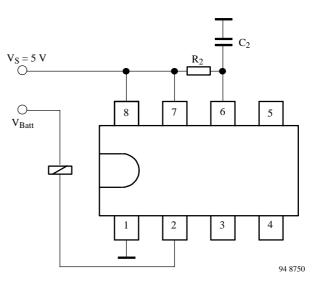


Figure 2b Basic circuit for $V_S = 5 V$

ΤΕΜΙΟ

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Oscillator, Pin 6

Oscillator frequency, f, is determined mainly by the R_2C_2 circuit. Resistance, R_2 , determines the charge time, and the integrated resistance (2 k Ω) is responsible for discharge time. For the stability of the oscillator frequency, it is recommended that the selected R_2 value be much greater than the internal resistance (2 k Ω), because the temperature response and the tolerances of the integrated resistance are considerably greater than the external resistance value.

Oscillator frequency, f, is calculated as follows:

$$f = \frac{1}{t_1 + t_2}$$

where

 $\begin{array}{l} t_1 = charge \ time = \alpha_1 \, . \, R_2 \, . \, C_2 \\ t_2 = discharge \ time = \alpha_2 \cdot 2 \ k\Omega \ \cdot \ C_2 \end{array}$

 α_1 and α_2 are constants as such

 $\alpha_1=0.833$ and $\alpha_2=1.551$ when $C_2=470~pF$ to 10 nF $\alpha_1=0.746$ and $\alpha_2=1.284$ when $C_2=10~nF$ to 4700 nF

Debounce time, t_3 , and the delay time, t_d , depend on the oscillator frequency, f, as follows:

$$t_{3} = 6 \cdot \frac{1}{f}$$
$$t_{d} = 73728 \cdot \frac{1}{f}$$

Table 1 shows relationships between t_3 , t_d , C_2 , R_2 and frequencies from 1 Hz to 20 kHz.

Relay control output

The relay control output is an open collector Darlington circuit with an integrated 23-V Z-diode for limitation of the inductive cut-off pulse of the relay coil. The maximum static collector current must not exceed 300 mA and saturation voltage is typically 1.1 V @ 200 mA.

Interference voltages and load dump

The IC supply is protected by R_1 , C_1 , and an integrated Z-diode, while the inputs are protected by a series resistor, integrated Z-diode and RF capacitor (refer to Figure 6).

The relay control output is protected via the integrated 23-V Z-diode in the case of short interference peaks. It is switched to conductive condition for a battery voltage of greater than approx. 40 V in the case of load dump. The output transistor is dimensioned so that it can withstand the current produced.

Power-on reset

When the operating voltage is switched on, an internal power-on reset pulse (POR) is generated which sets the logic of the circuits to a defined initial condition. The relay output is disabled.

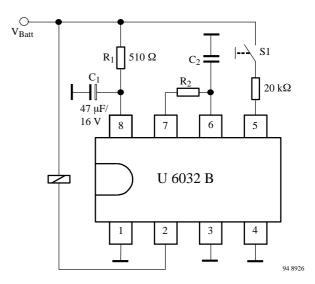


Figure 3 TOGGLE function

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Relay control output behaviour, Pin 2

Time functions (relay output) can be started or interrupted by the three inputs i.e., ON, OFF or TOGGLE (Pins 3, 4 and 5).

The relay becomes active if the time function is triggered, and the relay contact is interrupted after the elapse of delay time, t_d . There are two input possibilities:

Toggle input, figure 3

When the push-button (TOGGLE) switch, S_1 , is pressed for the first time, the relay becomes active after the debounce time, t_3 , i.e., the relay output, Pin 2, is active.

Renewed operation of S_1 causes the interruption of the relay contact and the relay is disabled. Each operation of the toggle switch, S_1 , changes (alters) the condition of the relay output when the debounce time, t_d , is exceeded i.e., the TOGGLE function.

If the relay output is not disabled by pressing the switch S_1 , the output is active.

ON, OFF inputs, Pins 3 and 4, fig. 4

To avoid simultaneous operation of both inputs, Pin 3 (ON) and Pin 4 (OFF), use of two-way contact with centre-off position with spring returns (also known as rocker-actuated switch) is recommended.

Pressing the push-button switch (Pin 3-ON) leads to the activation of the relay after the debounce time, t_3 , whereas the switching of the Pin 4 switch correspondingly leads to the relay being de-energized. If the relay is not de-energized by the push-button switch, the output remains active.

Combined operation, "TOGGLE and ON/OFF" is not possible due to the fact that there is only one debouncing circuit. Debouncing functions on both sides i.e., whenever S_1 is ON or OFF.

Figure 5 shows the input circuit of U 6032 B. It has an integrated pull-down resistance (20 k Ω), RF capacitor (15 pF) and Z-diode (7 V). It reacts to voltages greater than 2 V. The external protective resistor has a value of 20 k Ω and the push-button switch, S, is connected to the battery as shown in the diagram.

Contact current, I, is calculated as follows:

$$I = \frac{V_{Batt} - V_Z}{R(= 20 \text{ k}\Omega)} \text{ where } V_{Batt} = 12 \text{ V}, V_Z = 7 \text{ V}$$
$$I = \frac{(12-7) \text{ V}}{20 \text{ k}\Omega} \approx 0.25 \text{ mA}$$

It can be increased by connecting a 5.6 k Ω resistor from the push-button switch to ground as shown in figure 6.

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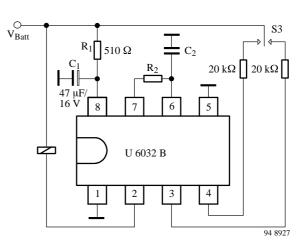


Figure 4 ON/OFF function

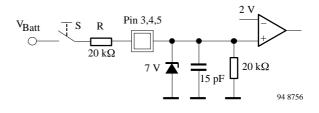


Figure 5 Input circuit

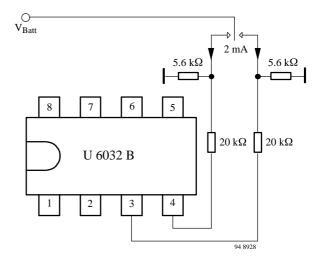


Figure 6 Increasing the contact current by parallel resistors

Absolute Maximum Ratings

Parameters	Symbol	Value	Unit
Operating voltage, static, 5 min	V _{Batt}	24	V
Ambient temperature range	T _{amb}	-40 to +125	°C
Storage temperature range	T _{stg}	-55 to +125	°C
Junction temperature	Tj	150	°C

Thermal Resistance

	Parameters	Symbol	Maximum	Unit
Junction ambient	DIP 8	T _{thJA}	110	K/W
	SO 8	T _{thJA}	160	K/W

Electrical Characteristics

V = 125	$V T = 25^{\circ}$	C mafamamaa	maint anound	figure 1	1101000	athomsico	manified
$V D_{0} t t \equiv [1, 1]$	V, $T_{amb} = 25^{\circ}$	C. reference	DOTHE PROUND.	ingure z.	umess	omerwise s	specified
Ball Pole	·, -amo -e	0,101010100	point Bround,			00000000000	peemea

Parameters	Test Conditions / Pin	Symbol	Min	Тур	Max	Unit
Operating voltage	$ \begin{array}{l} R_1 \geq 510 \ \Omega \\ t < 5 \ min \\ t < 60 \ min \end{array} $	V _{Batt}	6		16 24 18	V
5 V supply	Without R_1, C_1 figure 2bPins 7 and 8	V ₈ , V ₇	4.3		6.0	V
Stabilized voltage	$V_{Batt} = 12 V$ Pin 7	V ₇	5.0	5.2	5.4	V
Undervoltage threshold	Power on reset	Vs	3.0		4.2	V
Supply current	All pushbuttons open, Pin 8	IS		1.3	2.0	mA
Internal Z-diode	$I_8 = 10 \text{ mA} \qquad \text{Pin 8}$	VZ	13.5	14	16	V
Relay control output	Pin 2					
Saturation voltage	$I_2 = 200 \text{ mA}$ $I_2 = 300 \text{ mA}$	V ₂		1.2	1.5	V
Leakage current	$V_2 = 14 V$	I _{lkg}		2	100	μΑ
Output current		I ₂			300	mA
Output pulse current		•			•	
Load dump pulse	$t \le 300 \text{ ms}$	I ₂			1.5	A
Internal Z-diode	$I_2 = 10 \text{ mA}$	VZ	20	22	24	V
Oscillator input	f = 0.001 to 40 kHz, see table 1	Pin 6				•
Internal discharge resistance	V ₆ = 5 V	R ₆	1.6	2.0	2.4	kΩ
Switching voltage	Lower Upper	V _{6L} V _{6H}	0.9 2.8	1.1 3.1	1.4 3.5	V
Input current	$V_6 = 0 V$	-I ₆			1	μΑ
Switching times						
Debounce time		t3	5		7	cycles
Inputs ON, OFF, TOGGL	E Pins 3, 4 and 5					
Switching threshold voltage		V _{3,4,5}	1.6	2.0	2.4	V
Internal Z-diode	$I_{3, 4, 5} = 10 \text{ mA}$	V _{3,4,5}	6.5	7.1	8.0	V
Pull-down resistance	$V_{3,4,5} = 5 V$	R _{3,4,5}	13	20	50	kΩ

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Frequency f	Debounce time t ₃	C ₂	R ₂	Frequency f	Debounce time t ₃	C ₂	R ₂
Hz	ms	nF	kΩ	Hz	ms	nF	kΩ
1	6000	4700	280	700	9	10	170
2	3000	1000	650	800	8	10	150
3	2000	1000	440	900	7	10	130
4	1500	1000	330	1000	6	10	120
5	1200	1000	260	2000	3.00	1	600
6	1000	1000	220	3000	2.00	1	400
7	857	1000	190	4000	1.50	1	300
8	750	1000	160	5000	1.20	1	240
9	667	1000	140	6000	1.00	1	200
10	600	1000	130	7000	.86	1	170
20	300	100	650	8000	.75	1	150
30	200	100	440	9000	.67	1	130
40	150	100	330	10000	.60	1	120
50	120	100	260	11000	.55	1	110
60	100	100	220	12000	.50	1	99
70	86	100	190	13000	.46	1	91
80	75	100	160	14000	.43	1	85
90	67	100	140	15000	.40	1	79
100	60	100	130	16000	.38	1	74
200	30	10	600	17000	.35	1	70
300	20	10	400	18000	.33	1	66
400	15	10	300	19000	.32	1	62
500	12	10	240	20000	.30	1	59
600	10	10	200		•		

Table 1 Oscillator frequency, debounce time, dimensioning

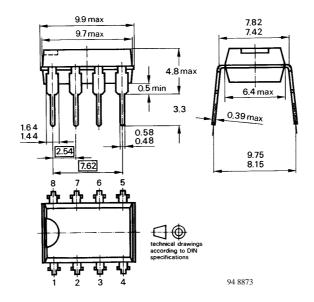
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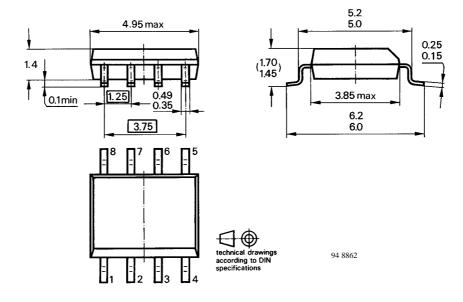
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Dimensions in mm

Package: DIP 8



Package: SO 8



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Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2831, Fax Number: 49 (0)7131 67 2423

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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements and
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

Of particular concern is the control or elimination of releases into the atmosphere of those substances which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) will soon severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of any ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA and
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with and do not contain ozone depleting substances.